

Giant enhancement of room-temperature magnetoresistance in $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3/\text{Nd}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ multilayers

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Abstract

The metal-insulator transition temperature in CMR manganites has been altered and brought close to the room temperature by preparing $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ (LSMO)/ $\text{Nd}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ (NSMO) multilayers with ultra thin individual layers of LSMO and NSMO. The LSMO/NSMO multilayers with ultra thin individual layers of thickness of about $10\text{\AA}$ exhibits 150% magnetoresistance at 270 K whereas LSMO/NSMO multilayers with moderate individual layer thickness of about $40\text{\AA}$ each exhibits a mere 15% magnetoresistance at the same temperature. We have shown that the reduction in thickness of the individual layers leads to increased spin fluctuation which results in the enhancement of magnetoresistance.

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Ever since the discovery of colossal magnetoresistance (CMR) in perovskite manganites¹, extensive research on the magneotransport properties of manganite films, multi-layers, tunnel junctions etc. has been initiated due to its potential for technological applications. The CMR manganites like $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ (LSMO), $\text{La}_{0.67}\text{Ca}_{0.33}\text{MnO}_3$ (LCMO), $\text{Nd}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ (NSMO) exhibit transition from a high temperature paramagnetic insulator to a low temperature ferromagnetic metal. In the ground state, these manganites are fully spin polarized² at the Fermi level. Encouraged by this high spin polarization, numerous efforts have been made to achieve room temperature MR using the extrinsic magnetoresistive properties such as the tunneling magnetoresistance (TMR)² phenomenon observed in manganite tunnel junctions or polycrystalline manganites. However it has been observed that for manganite tunnel junctions, the TMR falls off rapidly with increasing temperature³ and generally vanishes even before reaching the room temperature. Recently large room temperature magnetoresistance has been achieved in magnetic tunnel junctions with MgO as the tunnel barrier and Fe or CoFe as the electrodes^{4,5}. However, in such cases the insulating layer MgO needs to be a highly oriented single crystal, which is very difficult from the fabrication point of view. Moreover, the possibility of the transition metal electrodes having an oxidized and amorphous under-layer cannot be ruled out. Coming back to the half-metallic CMR manganites, although such materials produce high intrinsic MR around the Curie temperature, the fact that their critical temperatures are well away from the room temperature (for LSMO $T_c \sim 360$ K ; for NSMO $T_c \sim 220$ K; for LCMO $T_c \sim 250$ K) comes in the way of obtaining large MR around room temperature.

We have studied the magneto-transport properties of LSMO/NSMO multi-layers where the thickness of alternate LSMO and NSMO layers have been varied. This study attempts to bring the metal-insulator transition temperature, which is usually nearly coincident with the curie temperature, closer to the room temperature so that large MR can be obtained around the room temperature. We have obtained huge enhancement in magnetoresistance near room temperature by reducing the thickness of alternate layers in LSMO/NSMO magnetic multi-layer.

Four sets of samples have been prepared. Sample 1 is a LSMO film of thickness $3000\text{\AA}$ nm; sample 2 is a NSMO film of same thickness $3000\text{\AA}$ nm; sample 3 is the LSMO/NSMO multi-layer with alternate layer thickness $10\text{\AA}$ [LSMO($10\text{\AA}$)/NSMO($10\text{\AA}$)] and sample 4 is another LSMO/NSMO multilayer with alternate layer thickness of $40\text{\AA}$ [LSMO($40\text{\AA}$)/NSMO($40\text{\AA}$)]

and with LSMO as the top layer. Sample 4 will be used from now on as a reference. The total thickness of all the samples is about 3000 Å nm each. All the samples were prepared by pulsed laser deposition under identical conditions and deposited on LaAlO₃ substrate. X-ray diffraction confirms the epitaxial nature of the samples. The magnetotransport properties were studied using standard four probe method. The magnetic field was applied parallel to the applied electric field.

For sample 3, the resistivity curve in absence of magnetic field (Fig: 1) shows a distinct peak associated with metal-insulator transition at around 280 K. Considering the T_C of bulk LSMO and NSMO, this is a remarkable shift in transition temperature. Sample 1 and sample 4 show more or less the same feature with no metal-insulator transition below 300 K whereas sample 2 exhibits metal insulator transition at 220 K. The absolute value of resistivities at 3 K in samples 1, 2, 3 and 4 are 46 $\mu\Omega$ -cm, 200 $\mu\Omega$ -cm, 3950 $\mu\Omega$ -cm and 300 $\mu\Omega$ -cm, respectively. Since sample 1 and sample 4 exhibit almost similar magnetotransport properties and since sample 3 and sample 4 are similar samples with variation in individual layer thickness only, we shall primarily compare the properties of sample 3 with that of sample 4.

The resistivity data was analyzed using a polynomial expansion in temperature T. We have fitted the resistivity data for sample 3 and 4 with the following function

$$\frac{\rho(T)}{\rho(0)} = 1 + \beta T^2 + \gamma T^{4.5}$$

In the present case, the T^2 term comes from thermal spin fluctuation⁶ (of course electron-electron scattering can also give rise to such a term according to Fermi liquid theory⁷ for systems with high density of states at the fermi level). The $T^{4.5}$ temperature dependence has been predicted for electron-magnon scattering in the double exchange theory⁸. But the fitting is not very satisfactory at very low temperature where the resistivity is almost temperature independent with a very minor rise with lowering of temperature below 5 K. We also tried to fit with $T^{2.5}$ term instead of $T^{4.5}$ term to include electron-phonon scattering instead of electron magnon scattering but no improvement was observed. Henceforth we excluded the $T^{4.5}$ and $T^{2.5}$ term and the resistivity data was fitted considering the function

$$\frac{\rho(T)}{\rho(0)} = 1 + \beta T^2$$

in the temperature range above 5 K and below approximately $T_{MI}/2$. Most of the studies concerning transport properties of thin films of manganites have observed a dominant T^2

term at low temperature⁹, which is attributed to electron-electron interaction. Chen et. al.¹⁰ have fitted the ferromagnetic metallic region of the resistivity curve using small polaronic transport term $\sinh(C/T)$, C being a constant and a spin wave scattering term $T^{3.5}$. But in our case, the fitting is evidently poor when those terms are incorporated. To ascertain whether T^2 term is due to the predominance of spin fluctuations, we fitted the resistivity data for sample 3 and 4 with the above polynomial at different magnetic fields and studied the variation in β . The coefficient β decreases substantially with increasing magnetic field (Fig: 2). This suggests the suppression of spin fluctuation by applied magnetic field. The observed decrease in β with increasing magnetic field is more pronounced for sample 3 in comparison with sample 4. This indicates that the reduction in thickness of individual layers has resulted in enhanced spin fluctuation in sample 3 compared to sample 4.

The magnetic field dependence of magnetoresistance (MR) [$\{\rho(H) - \rho(0)\}/\rho(H)(\%)$] for sample 3 and 4 at 3 K shows contrasting behavior in the low and high magnetic field region (Fig: 4: Inset). In the low magnetic field region, a sharp drop in resistivity with increasing magnetic field, associated with the suppression of domain wall scattering, is observed for sample 4 whereas sample 3 shows no low field magnetoresistance. In the high field region the MR for sample 4 almost saturates, whereas the MR for sample 3 exhibits linear magnetic field dependence. However, near the metal insulator transition temperature, enhancement of low field MR has been observed for sample 3 as compared to sample 4. About 8% MR around 270 K has been observed for sample 3 in a magnetic field of 5 kOe compared to a mere 1% for sample 4. The comparison of the temperature dependence of high field MR between sample 1, 3 and 4 is shown in Fig: 3. Enhancement of high field MR for sample 3 as compared to sample 1 and 4 is observed over the entire temperature range. For sample 3, the MR peaks at 270 K and then decreases with increasing temperature whereas the MR for sample 1 and 4 weakly increases up to 300 K, indicating that both the samples are still well below the ferromagnetic transition temperature. In contrast to about 15% MR at 270 K for samples 1 and 4, the MR for sample 3 at 270 K is about 150% in 80 kOe magnetic field. The MR peak at 270 K suggests that the curie temperature is very close to the metal-insulator transition temperature for sample 3 and that the magnetoresistive properties exhibited by sample 3 is purely intrinsic in nature. The temperature dependence of magnetization for sample 3 shows that indeed the curie temperature is at around 270 K (Fig: 3,inset). The separate transition temperatures at about 210 K and 350 K for the NSMO and LSMO layers

are evident from the temperature dependence of magnetization for sample 4 (Fig: 3,inset). At 300 K, the MR for sample 3 is about 75% whereas it is only about 25% for samples 1 and 4. We have also studied the magnetic field dependence of MR for sample 3 and 4 (Fig: 4) at 300 K. While the MR of sample 4 shows linear magnetic field dependence, the MR for sample 3 shows distinct $-H^2$ dependence up to about 30kOe. This suggests that the origin of enhanced MR in sample 3 is the increased spin fluctuation due to reduction in thickness of individual layers and the eventual suppression of spin fluctuation by external magnetic field as already enunciated at the beginning of the discussion.

To summarize, we have compared the magnetotransport properties between the two LSMO/NSMO multi-layers : LSMO(10Å)/NSMO(10Å) and LSMO(40Å)/NSMO(40Å), fabricated by us. The magnetotransport properties observed in both the multi-layers do not mimic the extrinsic inter-granular transport properties shown by ferromagnetic metal-insulator composites but are rather intrinsic in nature. Analyzing the resistivity data in the presence as well as in absence of magnetic field, we conclude that the reduction in thickness of the individual layers leads to increased spin fluctuation in LSMO(10Å)/NSMO(10Å) and the enhanced magnetoresistance is a consequence of suppression of spin fluctuation by applied magnetic field. Although no extrinsic magnetoresistive properties due to scattering by domain walls or spin polarized tunneling across grain boundaries has been observed, still enhancement of low field MR has also been achieved over a wide temperature range near room temperature for sample 3. At 270 K and 80 kOe magnetic field, LSMO(10Å)/NSMO(10Å) shows 150% magnetoresistance which becomes 75% at 300 K. The enhancement of high field magnetoresistance has been observed in LSMO(10Å)/NSMO(10Å) over the entire temperature range compared to LSMO(40Å)/NSMO(40Å) multi-layer and LSMO film. The results suggest that it is possible to achieve much higher MR around room temperature by tuning the individual layer thickness and exploring suitable materials.

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FIG. 1: Resistivity normalized at 3 K, as a function of temperature, are shown for all the samples. (The absolute values of resistivity at 3 K are mentioned in the text.) The dotted curve corresponds to sample 2, showing the T_{MI} at 220 K; sample 1 and sample 4 show similar temperature dependence of resistivity; whereas T_{MI} for sample 3 is at 280 K, nearabout room temperature.

FIG. 2: The resistivity curves in absence of magnetic field for samples 3 and 4 have been fitted using spin fluctuation model, i.e. $\frac{\rho(T)}{\rho(0)} = 1 + \beta T^2$. Variation of β with applied magnetic field for sample 3 and 4 is shown; relative decrease of β with applied magnetic field is greater for sample 3 compared to sample 4. Inset: The T^2 dependence of resistivity for sample 3 is shown by the continuous line.

FIG. 3: Temperature dependence of magnetoresistance at 80 kOe for samples 1, 3 and 4. Sample 1 and 4 exhibit almost identical temperature dependence. The MR for sample 3 at 270 K is about ten times compared to that of sample 1 and 4. Inset: Field cooled M vs. T curves at $H = 1$ kOe for sample 3 and sample 4.

FIG. 4: Magnetic field dependence of MR for sample 3 and sample 4 at 300 K. MR shows distinct $-H^2$ dependence up to 30 kOe for sample 3. Dotted line is the theoretical fit. Inset: Magnetoresistance as a function of magnetic field at 3 K for sample 3 and sample 4. The small low field magnetoresistance for sample 4 is due to suppression of domain wall scattering. In contrast, sample 3 shows no low field magnetoresistance and almost linear magnetic field dependence.

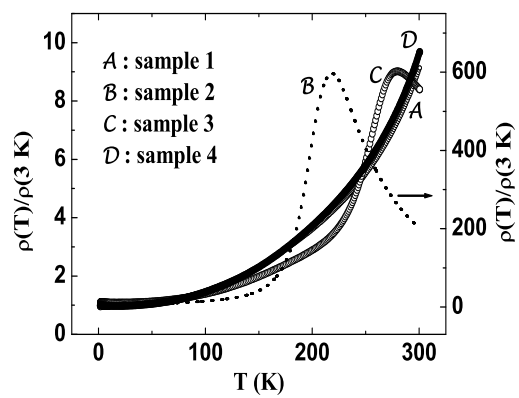


Fig. 1

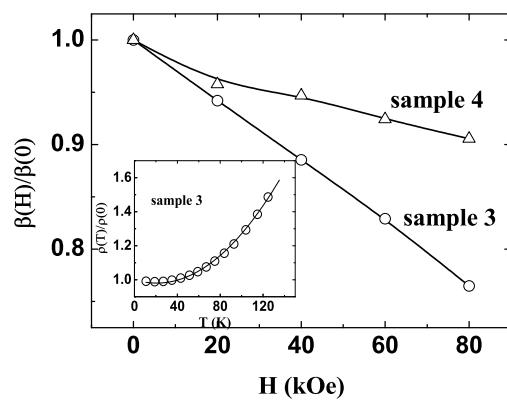


Fig. 2

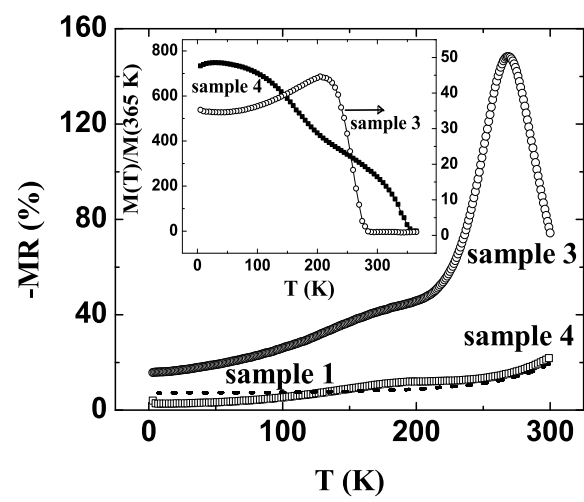


Fig. 3

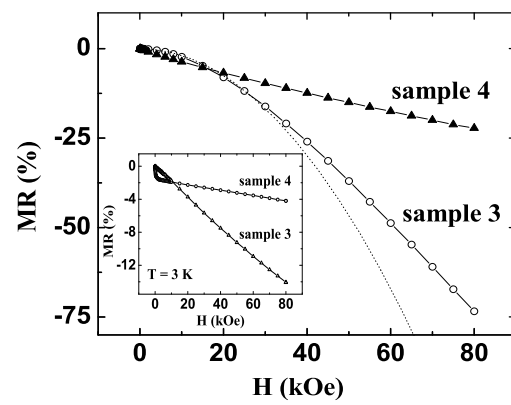


Fig. 4